



### 20V Complementary Enhancement Mode MOSFET

Voltage

20 / -20V

Current

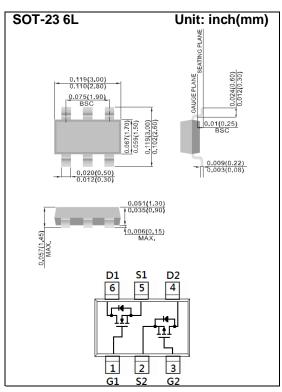
5.2 /-3.4A

### **Features**

- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std. (Halogen Free)

### **Mechanical Data**

- Case: SOT-23 6L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0005 ounces, 0.014 grams
- Marking: SC2



# **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	N-Ch LIMIT	P-Ch LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	20 -20		<b>V</b>
Gate-Source Voltage		$V_{GS}$	<u>+</u> 12 <u>+</u> 12		V
Continuous Drain Current		I <sub>D</sub>	5.2	-3.4	Α
Pulsed Drain Current (Note 4)		I <sub>DM</sub>	20.8	-13.6	Α
B	T <sub>a</sub> =25°C		1.25		W
Power Dissipation	Derate above 25°C	P <sub>D</sub>	1	mW/°C	
Operating Junction and Storage Temperature Range		$T_{J}, T_{STG}$	-55~150		°C
Typical Thermal Resistance					
- Junction to Ambient (Note 3)		$R_{\theta JA}$	10	°C/W	





### N-Channel Electrical Characteristics (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	20	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	0.5	0.77	1.2	V
Drain-Source On-State Resistance		V <sub>GS</sub> =4.5V, I <sub>D</sub> =5.2A	-	29	36	mΩ
	R <sub>DS(on)</sub>	V <sub>GS</sub> =2.5V, I <sub>D</sub> =3.2A	-	39	52	
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =1.5A	-	58	92	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =20V, $V_{GS}$ =0V	-	-	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 12V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 5)			_			
Total Gate Charge	$Q_{g}$	\/ 40\/ L 50A	-	4.1	-	nC
Gate-Source Charge	$Q_gs$	V <sub>DS</sub> =10V, I <sub>D</sub> =5.2A, V <sub>GS</sub> =4.5V <sup>(Note 1,2)</sup>	-	1.1	-	
Gate-Drain Charge	$Q_gd$	V <sub>GS</sub> =4.5V	-	0.7	-	
Input Capacitance	Ciss	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1.0MHZ	-	396	-	pF
Output Capacitance	Coss		-	54	-	
Reverse Transfer Capacitance	Crss		-	40	-	
Turn-On Delay Time	td <sub>(on)</sub>	\/ 40\/ L 5 0A	-	14	-	
Turn-On Rise Time	tr	$V_{DD}$ =10V, $I_{D}$ =5.2A, $V_{GS}$ =4.5V, $R_{G}$ =6 $\Omega$ (Note 1,2)	-	10	-	ns
Turn-Off Delay Time	td <sub>(off)</sub>		-	30	-	
Turn-Off Fall Time	tf		-	7	1	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	Is		-	-	1.5	А
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1.0A, V <sub>GS</sub> =0V		0.75	1.2	V

#### NOTES:

- 1. Pulse width<300us, Duty cycle<2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. ROJA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing





### **P-Channel Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static Static							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-20	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-0.4	-0.65	-1.2	V	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	$V_{GS}$ =-4.5V, $I_{D}$ =-3.4A	-	65	82	mΩ	
		$V_{GS}$ =-2.5V, $I_{D}$ =-2.2A	-	82	110		
		V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-1.2A	-	103	146		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V	-	-	-1	uA	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 12V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA	
Dynamic (Note 5)							
Total Gate Charge	$Q_g$	\/ 40\/ L 2.4A	-	7	-	nC	
Gate-Source Charge	$Q_gs$	$V_{DS}$ =-10V, $I_{D}$ =-3.4A, $V_{GS}$ =-4.5V (Note 1,2)	-	1	-		
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =-4.5V	-	1.8	-		
Input Capacitance	Ciss	V <sub>DS</sub> =-10V, V <sub>GS</sub> =0V, f=1.0MHZ	-	522	-	pF	
Output Capacitance	Coss		-	55	-		
Reverse Transfer Capacitance	Crss		-	40	-		
Turn-On Delay Time	td <sub>(on)</sub>	$V_{DD}$ =-10V, $I_{D}$ =-3.4A, $V_{GS}$ =-4.5V, $R_{G}$ =6 $\Omega$ (Note 1,2)	-	10	-	ns	
Turn-On Rise Time	tr		-	4	-		
Turn-Off Delay Time	td <sub>(off)</sub>		-	34	-		
Turn-Off Fall Time	tf		-	5	-		
Drain-Source Diode							
Maximum Continuous Drain-Source	,				1 5	_	
Diode Forward Current	I <sub>S</sub>		_	-	-1.5	A	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-1.0A, V <sub>GS</sub> =0V	-	0.77	-1.2	V	

### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. ROJA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
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### N-Channel TYPICAL CHARACTERISTIC CURVES

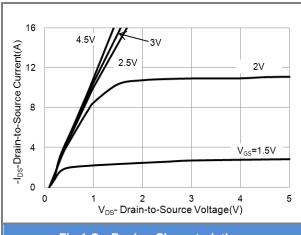


Fig.1 On-Region Characteristics

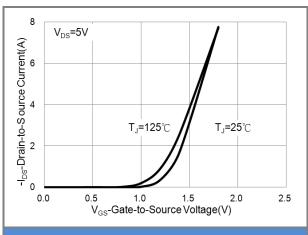


Fig.2 Transfer Characteristics

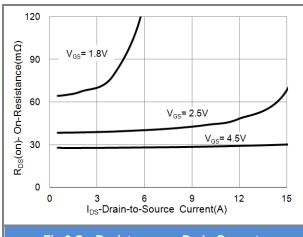


Fig.3 On-Resistance vs. Drain Current

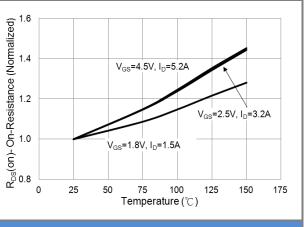
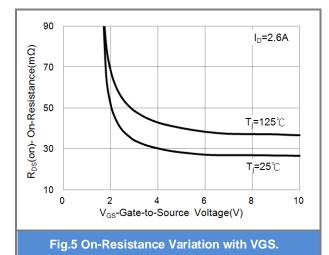
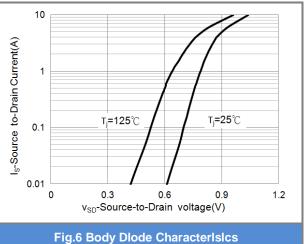


Fig.4 On-Resistance vs. Junction temperature









### N-Channel TYPICAL CHARACTERISTIC CURVES

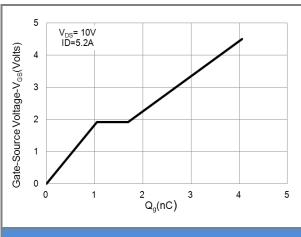


Fig.7 Gate-Charge Characteristics

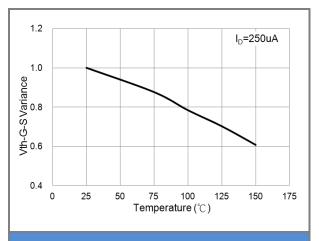


Fig.8 Threshold Voltage Variation with Temperature.

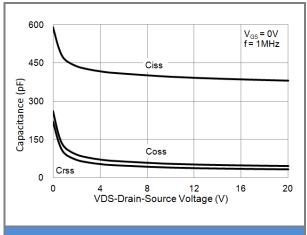


Fig.9 Capacitance vs. Drain-Source Voltage.





### P-Channel TYPICAL CHARACTERISTIC CURVES

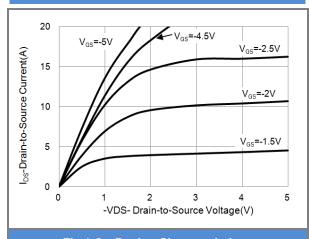
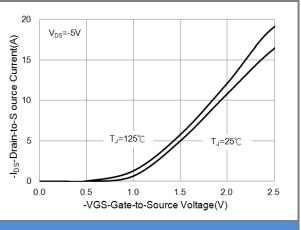


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

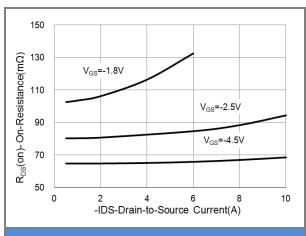


Fig.3 On-Resistance vs. Drain Current

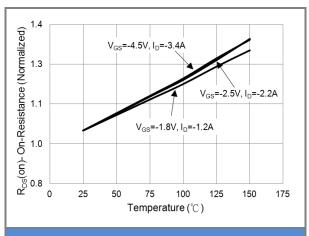
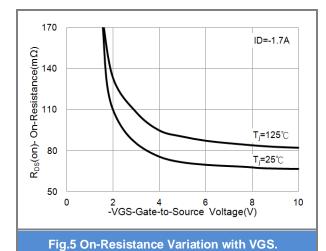
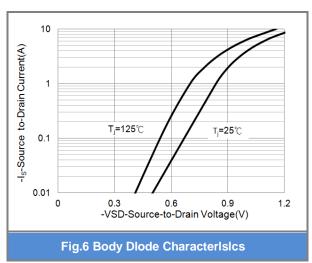


Fig.4 On-Resistance vs. Junction temperature









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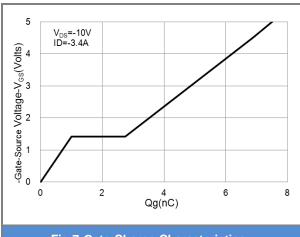


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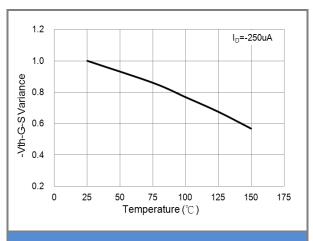


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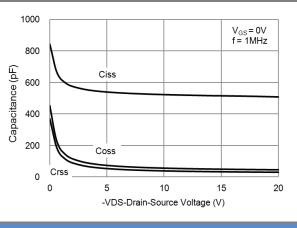


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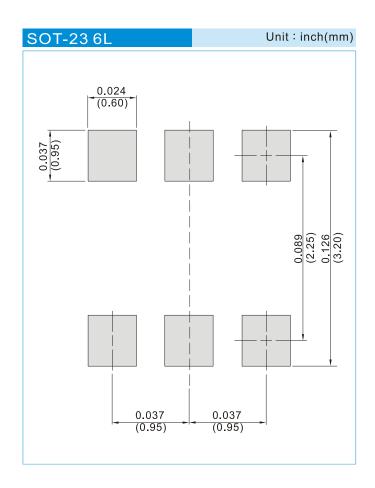




### PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJS6602_S1_00001	SOT-23 6L	3K pcs / 7" reel	SC2	Halogen free
PJS6602_S2_00001	SOT-23 6L	10K pcs / 13" reel	SC2	Halogen free

### **MOUNTING PAD LAYOUT**







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